

## WHAT IS CLAIMED IS:

1. A solid state image sensor comprising:
  2. a semiconductor substrate having an imaging area and a peripheral area defined thereon so that said peripheral area surrounds said imaging area;
  5. a field isolation dielectric formed as isolation regions on said substrate in said peripheral area;
  7. a gate insulating film formed on said substrate in said imaging area and surrounded by said field isolation dielectric;
  9. a plurality of vertical and horizontal shift register electrodes formed on said gate insulating film in said imaging area and on said field isolation dielectric in said peripheral area, said plurality of vertical and horizontal shift register electrodes being made from a single layer of conductor;
  14. photoelectric conversion elements formed in said substrate, each element being surrounded by said vertical shift register electrode;
  17. an interlayer insulation film having a planarized surface and covering said plurality of vertical and horizontal shift register electrodes, as well as gaps between said plurality of vertical and horizontal shift register electrodes, said interlayer insulation film being formed on said gate insulating film on each of said photoelectric conversion elements and formed lower than said vertical shift register electrode on each of said photoelectric conversion elements; and
  25. a light shielding metal layer provided on said interlayer insulation film on said plurality of vertical and horizontal shift register electrodes and having openings above said photoelectric conversion elements, said light shielding metal layer serving as interconnects for making electrical connection

30 to said plurality of vertical and horizontal shift register  
31 electrodes in said peripheral area.

1       2. The solid state image sensor according to claim 1,  
2 wherein a distance between adjacent electrodes out of said  
3 plurality of vertical and horizontal shift register electrodes  
4 in said peripheral area is larger than a distance between adjacent  
5 electrodes out of said plurality of first and second shift  
6 register electrodes in said imaging area.

1       3. The solid state image sensor according to claim 1,  
2 wherein said interlayer insulation film on said plurality of  
3 vertical and horizontal shift register electrodes in said imaging  
4 area is thinner than said interlayer insulation film on said  
5 plurality of vertical and horizontal shift register electrodes  
6 in said peripheral area.

1       4. The solid state image sensor according to claim 1,  
2 wherein said interlayer insulation film on said plurality of  
3 vertical and horizontal shift register electrodes in said  
4 peripheral area and said interlayer insulation film on said  
5 plurality of second shift register electrodes in said imaging  
6 area have the same thickness and wherein said interlayer  
7 insulation film on said plurality of first shift register  
8 electrodes in said imaging area is thinner than said interlayer  
9 insulation film on said plurality of vertical and horizontal  
10 shift register electrodes in said peripheral area.

1       5. The solid state image sensor according to claim 1,  
2 wherein said plurality of vertical shift register electrodes  
3 in said imaging area serve as a readout electrode used to transfer

4       electrical charge generated in each of said photoelectric  
5       conversion elements to a shift register channel below said  
6       plurality of vertical shift register electrodes.

1       6. The solid state image sensor according to claim 1,  
2       further comprising a vertical shift register channel below said  
3       plurality of vertical shift register electrodes and a horizontal  
4       shift register channel below said plurality of horizontal shift  
5       register electrodes.

1       7. The solid state image sensor according to claim 1,  
2       wherein a surface portion of said plurality of vertical and  
3       horizontal shift register electrodes in said imaging area is  
4       a silicide layer.

1       8. A solid state image sensor comprising:  
2            a semiconductor substrate having an imaging area and a  
3            peripheral area defined thereon so that said peripheral area  
4            surrounds said imaging area;  
5            a field isolation dielectric formed as isolation regions  
6            on said substrate in said peripheral area;  
7            a gate insulating film formed on said substrate in said  
8            imaging area and surrounded by said field isolation dielectric;  
9            a plurality of shift register electrodes formed on said  
10          gate insulating film in said imaging area and on said field  
11          isolation dielectric in said peripheral area;  
12          photoelectric conversion elements formed in said  
13          substrate in said imaging area, each element being surrounded  
14          by said shift register electrode; and  
15          an interlayer insulation film having a planarized surface  
16          and covering said plurality of shift register electrodes, as

17 well as gaps between said plurality of shift register electrodes,  
18 said interlayer insulation film being formed on said gate  
19 insulating film on each of said photoelectric conversion elements  
20 and formed lower than said shift register electrode surrounding  
21 each of said photoelectric conversion elements.

1        9. The solid state image sensor according to claim 8,  
2 wherein said plurality of shift register electrodes are made  
3 from a single layer of conductor.

1        10. The solid state image sensor according to claim 8,  
2 wherein a distance between adjacent electrodes out of said  
3 plurality of shift register electrodes in said peripheral area  
4 is larger than a distance between adjacent electrodes out of  
5 said plurality of shift register electrodes in said imaging area.

1        11. The solid state image sensor according to claim 8,  
2 further comprising a light shielding metal layer provided on  
3 said interlayer insulation film on said plurality of shift  
4 register electrodes, wherein said light shielding metal layer  
5 has openings above said photoelectric conversion elements and  
6 serves as interconnects for making electrical connection to said  
7 plurality of shift register electrodes in said peripheral area.

1        12. The solid state image sensor according to claim 8,  
2 wherein said plurality of shift register electrodes comprises  
3 a plurality of vertical and horizontal shift register electrodes  
4 and wherein said plurality of vertical shift register electrodes  
5 are disposed adjacent said photoelectric conversion elements  
6 to retrieve electrical charge generated in said photoelectric  
7 conversion elements.

1           13. The solid state image sensor according to claim 12,  
2   wherein said interlayer insulation film covers said plurality  
3   of vertical and horizontal shift register electrodes and gaps  
4   between said plurality of vertical and horizontal shift register  
5   electrodes and wherein said interlayer insulation film on said  
6   plurality of vertical and horizontal shift register electrodes  
7   in said imaging area is thinner than said interlayer insulation  
8   film on said plurality of vertical and horizontal shift register  
9   electrodes in said peripheral area.

1           14. The solid state image sensor according to claim 12,  
2   wherein said interlayer insulation film covers said plurality  
3   of vertical and horizontal shift register electrodes, as well  
4   as gaps between said plurality of vertical and horizontal shift  
5   register electrodes in said imaging area and wherein said  
6   interlayer insulation film on said plurality of vertical and  
7   horizontal shift register electrodes in said peripheral area  
8   and said interlayer insulation film on said plurality of  
9   horizontal shift register electrodes are the same in thickness,  
10   and wherein said interlayer insulation film on said plurality  
11   of vertical shift register electrodes in said imaging area is  
12   thinner than said interlayer insulation film on said plurality  
13   of vertical and horizontal shift register electrodes in said  
14   peripheral area.

1           15. The solid state image sensor according to claim 12,  
2   further comprising a vertical shift register channel below said  
3   plurality of vertical shift register electrodes and a horizontal  
4   shift register channel below said plurality of horizontal shift  
5   register electrodes.

1        16. The solid state image sensor according to claim 12,  
2        wherein a surface portion of said plurality of vertical and  
3        horizontal shift register electrodes is silicide layer.

1        17. A solid state image sensor comprising:  
2            a semiconductor substrate having an imaging area and a  
3            peripheral area surrounding said imaging area;  
4            a field isolation dielectric formed on said peripheral  
5            area to define said imaging area;  
6            a plurality of photoelectric conversion elements formed  
7            in said imaging area, each of said photoelectric conversion  
8            elements having an insulating film formed on an associated part  
9            of said imaging area;  
10          a charge transfer section provided in said imaging area  
11          to transfer charges generated by said photoelectric conversion  
12          elements, said charge transfer section having a plurality of  
13          shift register electrodes, each of shift register electrodes  
14          being elongated over said field isolation dielectric to form  
15          an elongated portion;  
16          an interlayer insulation film covering the elongated  
17          portion of said each of said shift register electrodes so that  
18          said interlayer insulation film in said peripheral area is  
19          thicker than said insulating film of each of said photoelectric  
20          conversion elements; and  
21          a conductive layer formed on said interlayer insulation  
22          film to cross the elongated portion of said each of said shift  
23          register electrodes.

1        18. The solid state image sensor according to claim 17,  
2        wherein said plurality of shift register electrodes are made

3 from a single layer of conductor.

1        19. The solid state image sensor according to claim 17,  
2 wherein the elongated portions of said shift register electrodes  
3 are arranged such that a distance between adjacent elongated  
4 portions in said peripheral area is larger than a distance between  
5 adjacent elongated portions in said imaging area.

1        20. The solid state image sensor according to claim 17,  
2 wherein said charge transfer section comprises vertical and  
3 horizontal charge transfer sections and wherein said interlayer  
4 insulation film on said elongated portions in said horizontal  
5 charge transfer section and said interlayer insulation film on  
6 said elongated portions in said peripheral area are the same  
7 in thickness, and wherein said interlayer insulation film on  
8 said elongated portions in said vertical charge transfer section  
9 is thinner than said interlayer insulation film on said elongated  
10 portions in said peripheral area.